

# Damir Borovac

## List of Publications by Year in descending order

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Version: 2024-02-01

22  
papers

142  
citations

1306789

7  
h-index

1199166

12  
g-index

22  
all docs

22  
docs citations

22  
times ranked

112  
citing authors

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 1  | InGaN/Dilute-As GaNAs Interface Quantum Well for Red Emitters. Scientific Reports, 2016, 6, 19271.   | 1.6 | 29        |
| 2  | First-Principle Electronic Properties of Dilute-P GaN <sub>1-x</sub> P <sub>x</sub> Alloy for Visible Light Emitters. Scientific Reports, 2016, 6, 24412.  | 1.6 | 15        |
| 3  | Thermal Oxidation of AlInN for III-Nitride Electronic and Optoelectronic Devices. ACS Applied Electronic Materials, 2019, 1, 1367-1371.  | 2.0 | 12        |
| 4  | Recombination rates in green-yellow InGaN-based multiple quantum wells with AlGaIn interlayers. Journal of Applied Physics, 2019, 126, .   | 1.1 | 12        |
| 5  | On the thermal stability of nearly lattice-matched AlInN films grown on GaN via MOVPE. Journal of Crystal Growth, 2020, 533, 125469.   | 0.7 | 11        |
| 6  | Band Anti-Crossing Model in Dilute-As GaNAs Alloys. Scientific Reports, 2019, 9, 5128.   | 1.6 | 9         |
| 7  | Dilute-As AlNAs Alloy for Deep-Ultraviolet Emitter. Scientific Reports, 2016, 6, 22215.  | 1.6 | 8         |
| 8  | Investigations of the Optical Properties of GaNAs Alloys by First-Principle. Scientific Reports, 2017, 7, 17285.   | 1.6 | 7         |
| 9  | Low background doping in AlInN grown on GaN via metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2020, 548, 125847.  | 0.7 | 7         |
| 10 | First-Principle Study of the Optical Properties of Dilute-P GaN <sub>1-x</sub> P <sub>x</sub> Alloys. Scientific Reports, 2018, 8, 6025.   | 1.6 | 6         |
| 11 | Thermal oxidation rates and resulting optical constants of Al <sub>0.83</sub> In <sub>0.17</sub> N films grown on GaN. Journal of Applied Physics, 2021, 129, .  | 1.1 | 6         |
| 12 | AlInN/GaN diodes for power electronic devices. Applied Physics Express, 2020, 13, 091006.  | 1.1 | 6         |
| 13 | First-principle electronic properties of dilute-P AlNP deep ultraviolet semiconductor. AIP Advances, 2018, 8, .  | 0.6 | 4         |
| 14 | Controlled growth of InGaN quantum dots on photoelectrochemically etched InGaIn quantum dot templates. Journal of Crystal Growth, 2020, 540, 125652.   | 0.7 | 3         |
| 15 | Electronic properties of dilute-As InGaNAs alloys: A first-principles study. Journal of Applied Physics, 2020, 127, .  | 1.1 | 2         |
| 16 | Recombination Rates of In <sub>x</sub> Ga <sub>1-x</sub> N/Al <sub>y</sub> Ga <sub>1-y</sub> N/GaN Multiple Quantum Wells Emitting From 640 to 565 nm. IEEE Journal of Quantum Electronics, 2021, 57, 1-7. | 1.0 | 2         |
| 17 | Experimental Studies of Delta-InN Incorporation in InGaIn Quantum Well for Long Wavelength Emission. , 2018, , .   |     | 1         |
| 18 | Prospects for hole doping in dilute-anion III-nitrides. Applied Physics Letters, 2021, 118, .  | 1.5 | 1         |

| #  | ARTICLE  | IF  | CITATIONS |
|----|--|-----|-----------|
| 19 | Dilute-As InGaNaNs/GaN Quantum Wells for High-Efficiency Red Emitters. IEEE Journal of Quantum Electronics, 2022, 58, 1-6. | 1.0 | 1         |
| 20 | Dilute-anion III-nitride: A potential visible light emitter. , 2016, , .   |     | 0         |
| 21 | Investigation of Band Anticrossing Parameters for Dilute-Anion III-Nitride Alloys. , 2019, , .                             |     | 0         |
| 22 | Gain Properties of Dilute-As InGaNaNs Quantum Wells for Red-Emitting Lasers. , 2021, , .                                   |     | 0         |